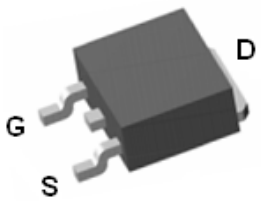
UNIKC Semiconductor

P0425HDB

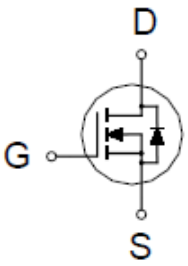
N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
250V	1.1Ω @V_{GS} = 10V	4A



TO-252



100% UIS tested

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	250	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current[2]	T_C = 25 °C	I_D	4	A
	T_C = 100 °C		2.4	
Pulsed Drain Current[1,2]		I_{DM}	15	
Avalanche Current[3]		I_{AS}	0.6	
Avalanche Energy[3]		E_{AS}	0.2	mJ
Power Dissipation	T_C = 25 °C	P_D	43	W
	T_C = 100 °C		17	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	$R_{\theta JA}$		62.5	°C / W
Junction-to-Case	$R_{\theta JC}$		2.9	

[1]Pulse width limited by maximum junction temperature.

[2]Limited only by maximum temperature allowed

[3]V_{DD} = 50V , L = 1mH, starting T_J = 25°C

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	250			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1	2.1	3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Gate Voltage Drain Current	I_{DSS}	V_{DS} = 250V, V_{GS} = 0V, T_C = 25 °C			1	μA
		V_{DS} = 200V, V_{GS} = 0V, T_C = 100 °C			10	
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 10V , I_D = 2A		0.81	1.1	Ω
		V_{GS} = 4.5V, I_D = 2A		0.98	1.7	
Forward Transconductance[1]	g_{fs}	V_{DS} = 10V, I_D = 2A		3		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		170		pF
Output Capacitance	C_{oss}			42		
Reverse Transfer Capacitance	C_{rss}			10		
Total Gate Charge[2]	Q_g	V_{DD} = 200V, I_D = 4A,V_{GS} = 10V		6.2		nC
Gate-Source Charge[2]	Q_{gs}			1		
Gate-Drain Charge[2]	Q_{gd}			2.7		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DD} = 125V, I_D = 4A, V_{GS} = 10V		10		nS
Rise Time[2]	t_r			6		
Turn-Off Delay Time[2]	$t_{d(off)}$			14		
Fall Time[2]	t_f			3		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current[3]	I_S				4	A
Forward Voltage[1]	V_{SD}	I_F = 4A, V_{GS} = 0V			1.5	V
Reverse Recovery Time	t_{rr}	I_F = 4A, dI_F/dt = 100A / μS		115		nS
Reverse Recovery Charge	Q_{rr}			370		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2]Independent of operating temperature.

[3]Pulse width limited by maximum junction temperature.

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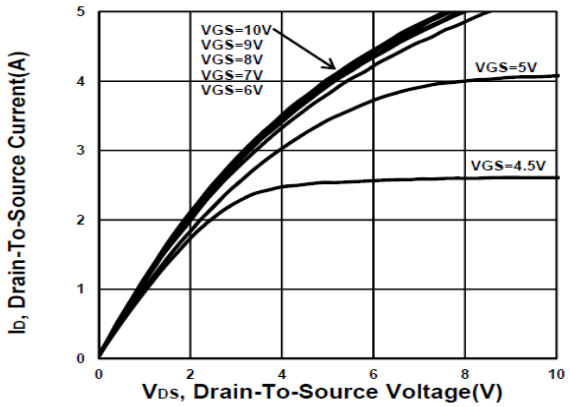
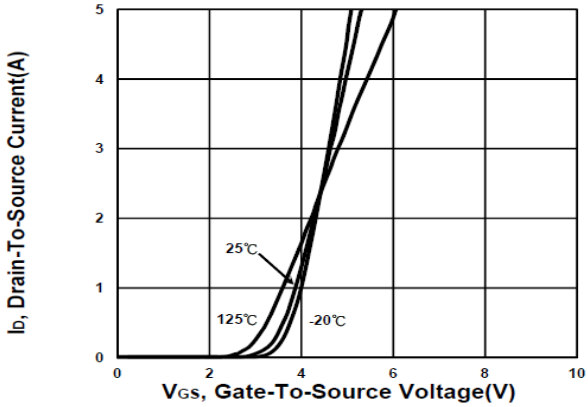
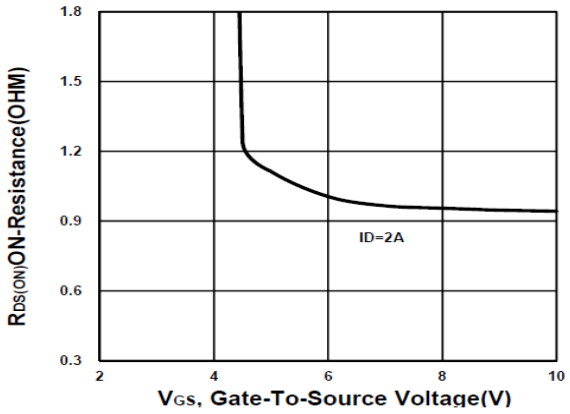
Output Characteristics



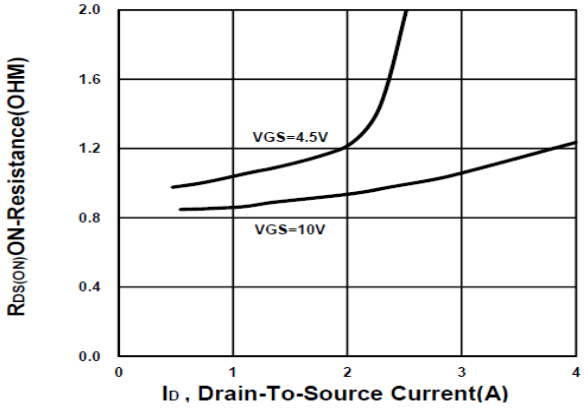
Transfer Characteristics



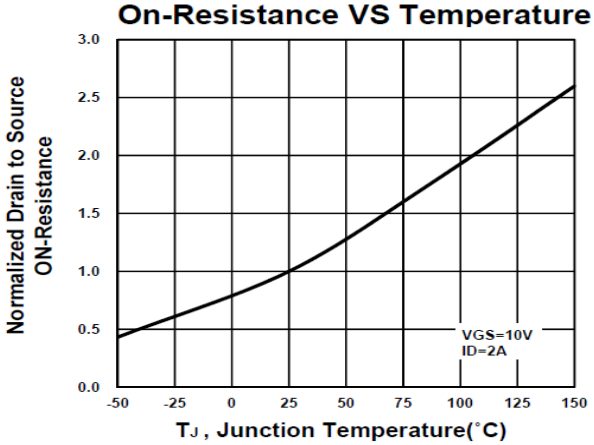
On-Resistance VS Gate-To-Source



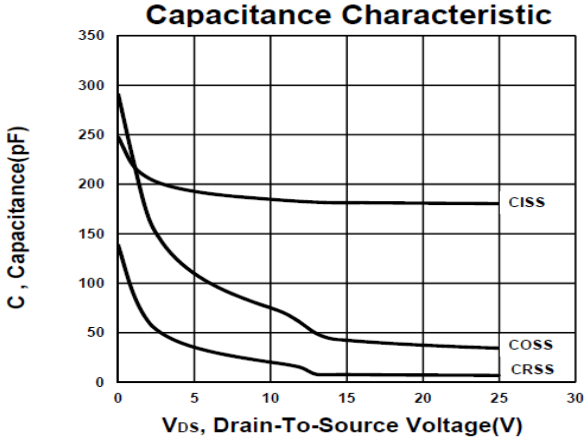
On-Resistance VS Drain Current



On-Resistance VS Temperature



Capacitance Characteristic



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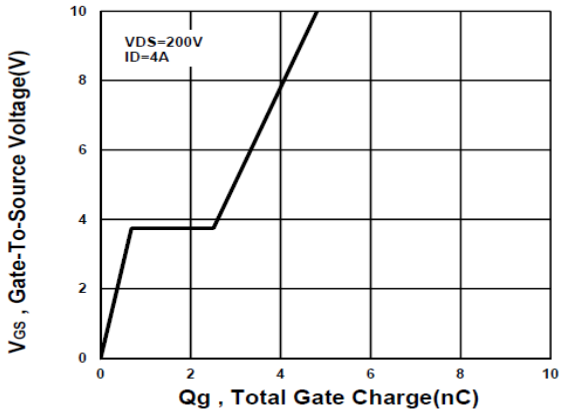
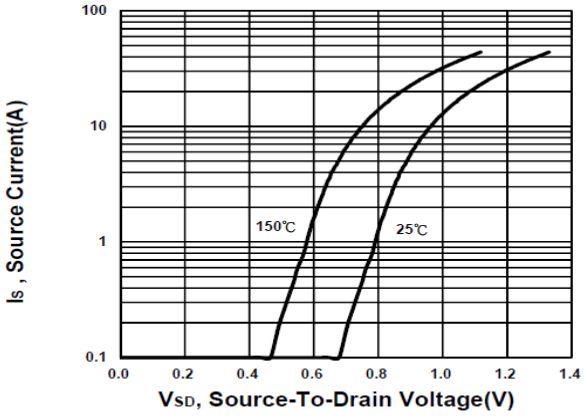
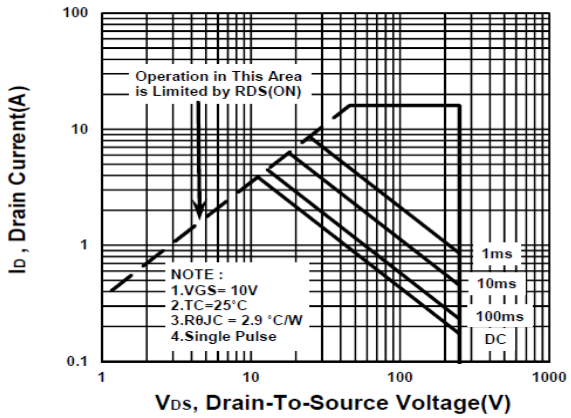
Gate charge Characteristics



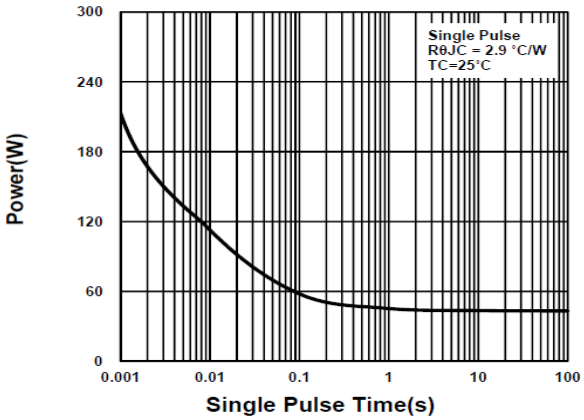
Source-Drain Diode Forward Voltage



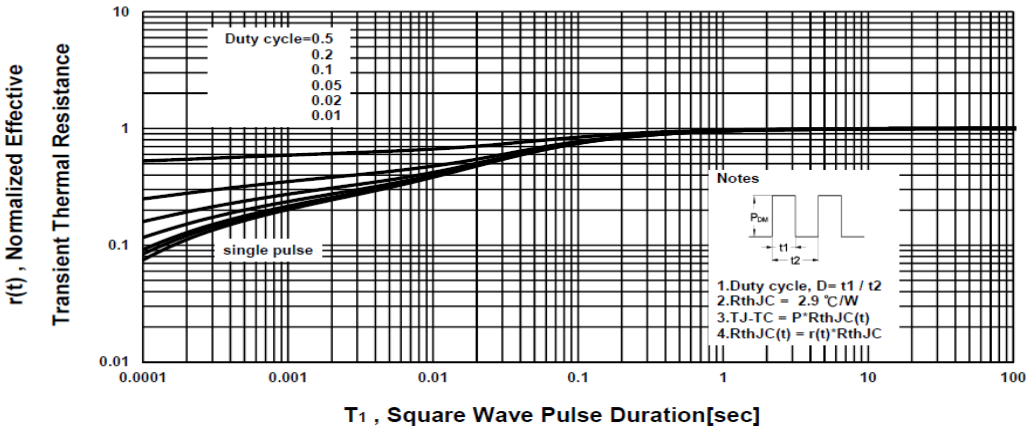
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



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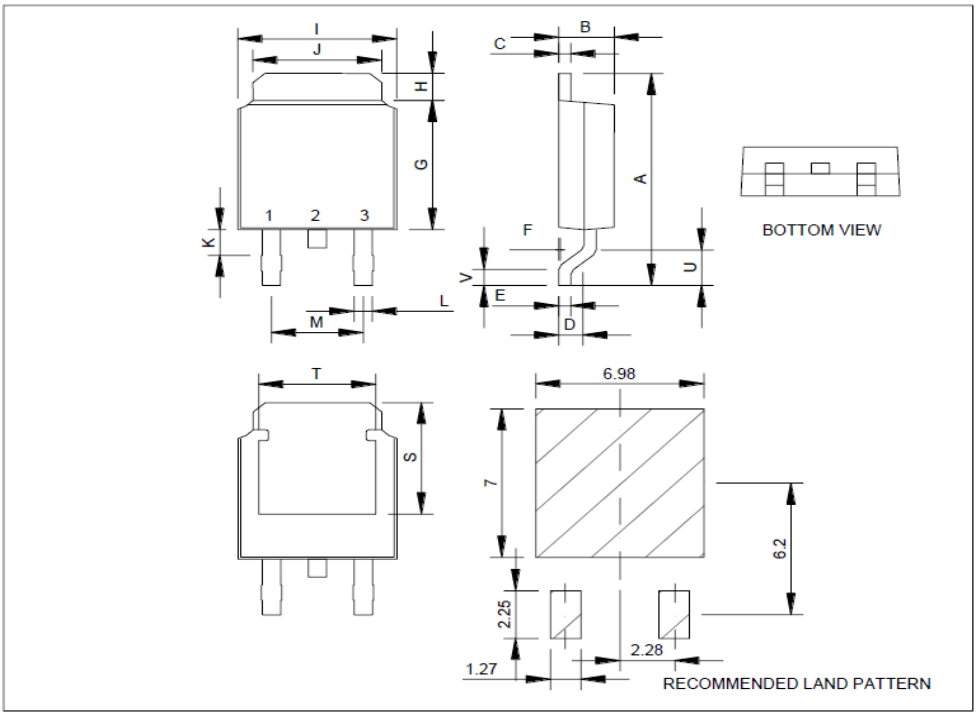
Package Dimension

TO-252 (DPAK) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	8.9	10	10.41	J	4.8		5.64
B	2.1	2.2	2.4	K	0.15		1.1
C	0.4	0.5	0.61	L	0.4	0.76	0.89
D	0.82	1.2	1.5	M	4.2	4.58	5
E	0.4	0.5	0.61	S	4.9	5.1	5.3
F	0		0.2	T	4.6	4.75	5.44
G	5.3	6.1	6.3	U	1.4		1.78
H	0.9		1.7	V	0.55	1.25	1.7
I	6.3	6.5	6.8				



*因为各家封装模具不同而外观略有所差异，不影响电性及Layout。

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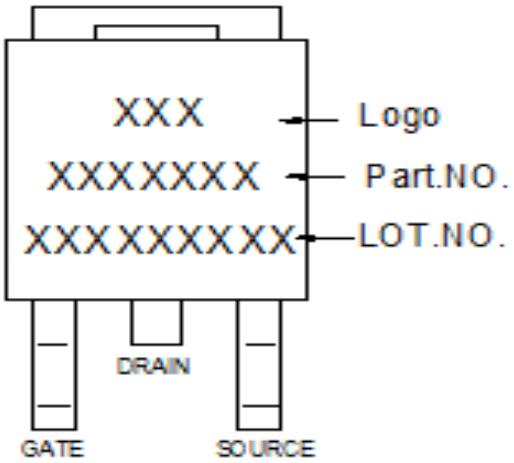
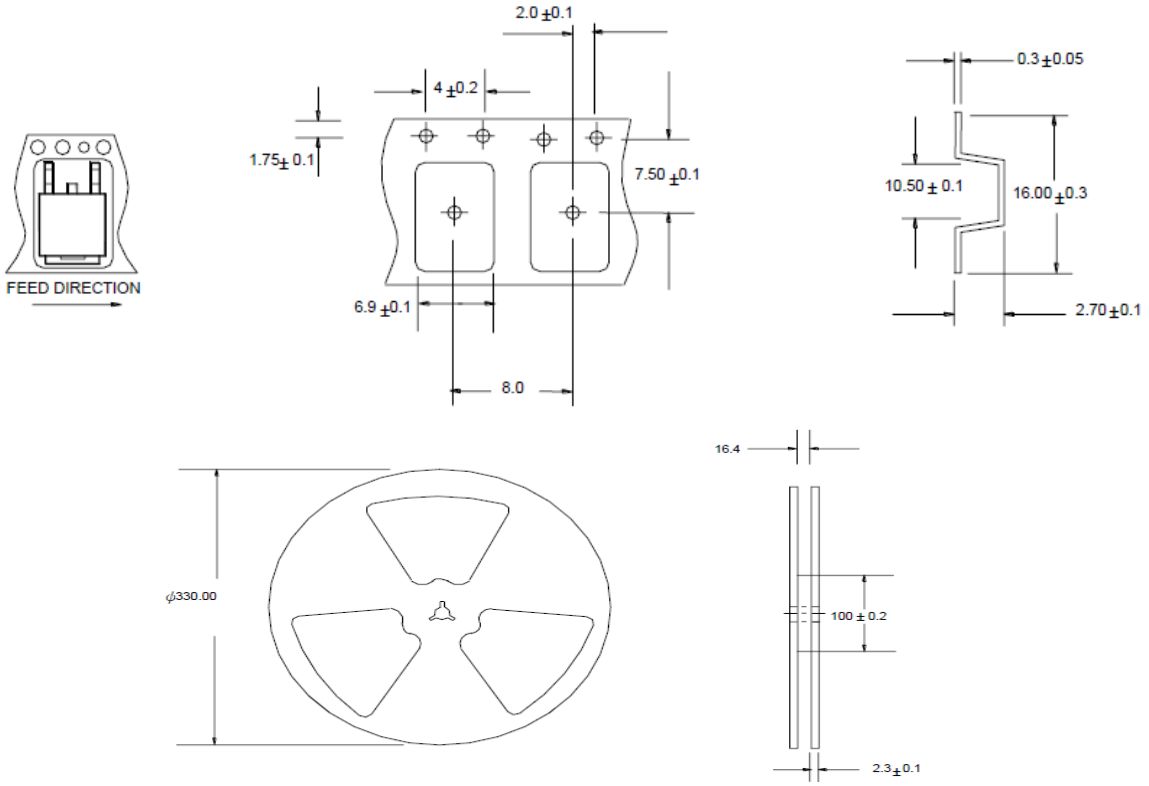
A. Marking Information



B. Tape&Reel Information:2500pcs/Reel



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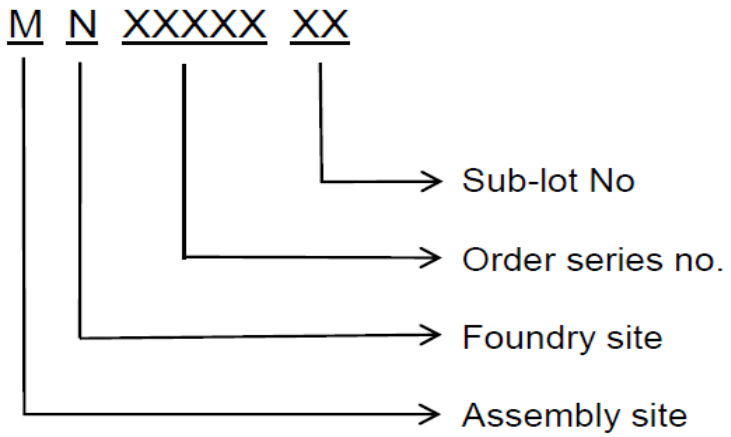
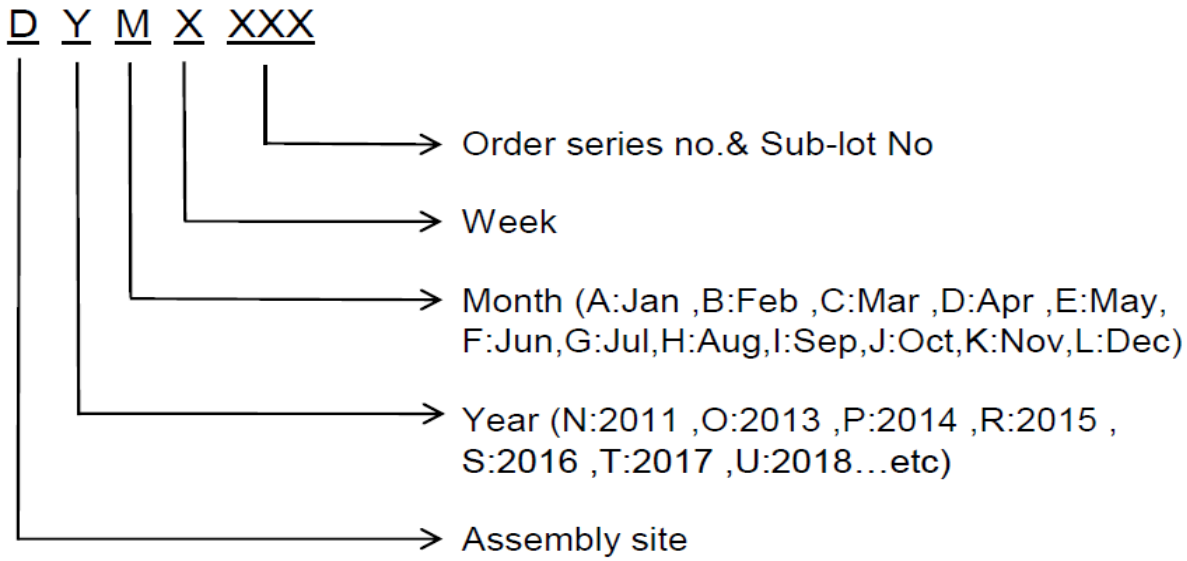
C. Lot No.&Date Code rule

1.Lot No.



2.Date Code



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D.Label rule

标签内容(Label content)

1	Label Size	30 * 90 mm
2	Font style	Times New Roman or Arial (或可区分英文”O”和数字”0”，”G和”Q”的字型即可)
3	U-NIKC	Height: 4 mm
4	Package	Height: 2 mm
5	Date	Height: 2 mm Shipping date: YYYY/MM/DD, ex. 2008/09/12
6	Device	Height: 3 mm (Max: 16 Digit)
7	Lot	Height: 3 mm (Max: 9 Digit) Sub lot
8	D/C	Height: 3 mm (Max: 7 Digit)
9	QTY	Height: 3 mm (Max: 6 Digit) Thousand mark is no needed
10	RoHS label	RoHS long axis: 12 mm minor axis:6 mm bottom color: White Font color: Black Font style: Arial
11	Halogen Free label	G Diameter: 10 mm bottom color: Green Font color: Black Font style: Arial
12	Scan information	Device / Lot / D/C / QTY , Insert “ / “ between every parts. for example: P3055LDG/G12345601/GGG2301/2000 DPI (Dots per inch): Over 300 dpi Code : Code 128 Height: 6 mm at least